

NPN SILICON RF TRANSISTOR

DESCRIPTION:

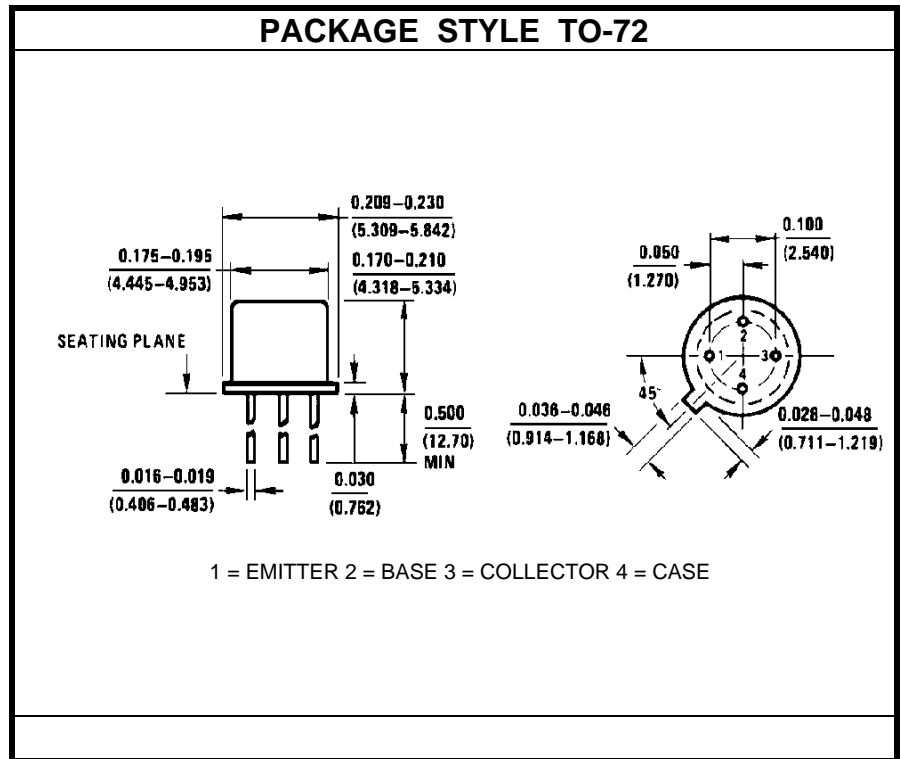
The **ASI MRF904** is Designed for General Purpose Amplifier Applications.

FEATURES:

- NF = 1.5 dB (Typ) 450 MHz
- G_{max} = 16 dB (Typ) 450 MHz
- f_T = 4.0 GHz (Typ) @ I_C = 15 mA

MAXIMUM RATINGS

I_C	30 mA
V_{CBO}	25 V
V_{CEO}	15 V
P_{DISS}	0.2 W @ $T_A = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 1.0\text{ mA}$			15			V
BV_{CBO}	$I_C = 100\text{ }\mu\text{A}$			25			V
BV_{EBO}	$I_E = 100\text{ }\mu\text{A}$			3.0			V
I_{CBO}	$V_{CB} = 15\text{ V}$					50	nA
h_{FE}	$V_{CE} = 5.0\text{ V}$	$I_C = 5.0\text{ mA}$		30		200	---
C_{OB}	$V_{CB} = 10\text{ V}$	$f = 1.0\text{ MHz}$				1.0	pF
f_T	$V_{CE} = 10\text{ V}$	$I_C = 15\text{ mA}$	$f = 1.0\text{ GHz}$		4.0		GHz
NF G_{max}	$V_{CE} = 6.0\text{ V}$	$I_C = 5.0\text{ mA}$	$f = 450\text{ MHz}$		1.5		dB
					16		dB
NF G_{max}	$V_{CE} = 6.0\text{ V}$	$I_C = 5.0\text{ mA}$	$f = 1.0\text{ GHz}$		2.5		dB
					10		dB